

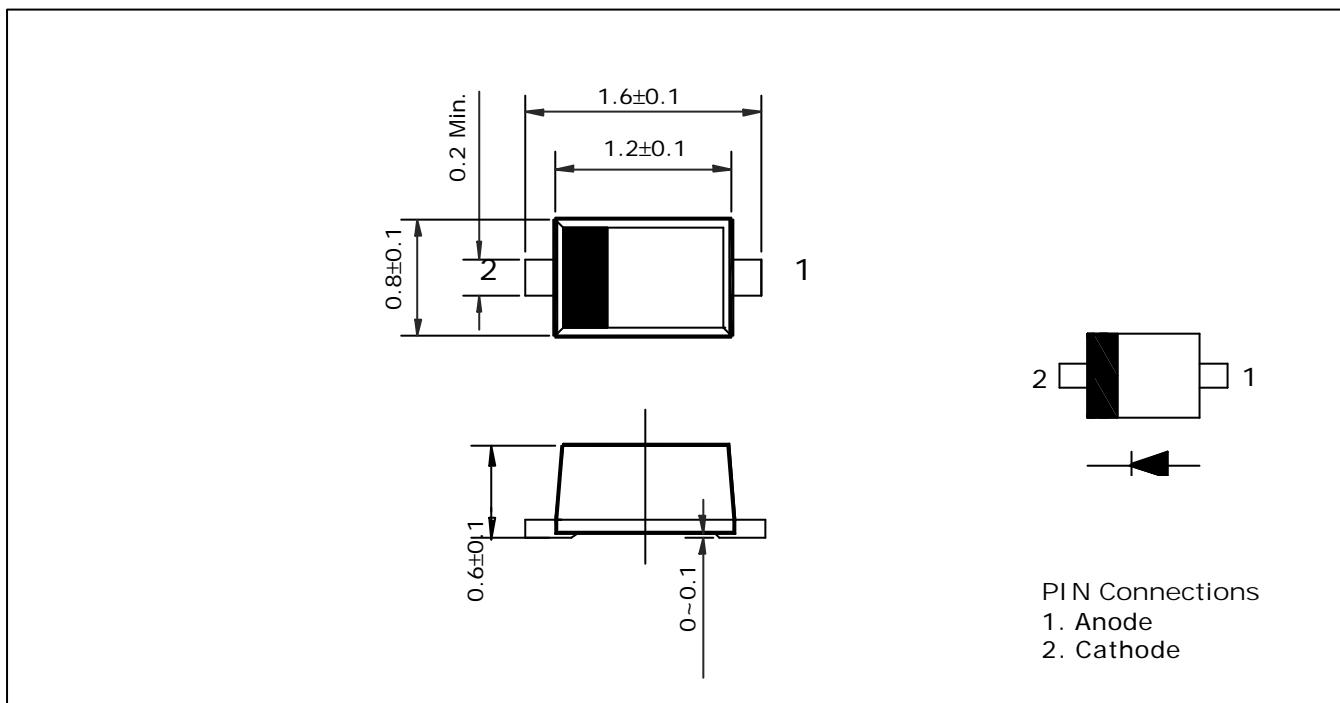
## Features

- Low power rectified
- Silicon epitaxial type
- Battery changing diode

## Ordering Information

Type No.	Marking	Package Code
SDB110Q	S3	SOD-523

## Outline Dimensions

**unit : mm**

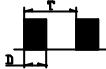
**Absolute maximum ratings**

(Ta=25°C)

Characteristic	Symbol	Ratings	Unit
Reverse voltage	V <sub>R</sub>	10	V
Repetitive peak forward current	I <sub>FRM</sub> <sup>*</sup>	0.5	A
Forward current	I <sub>F</sub>	30	mA
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 ~ 150	°C

\* :  $\delta = D/T = 0.33$ 

(T&lt;1S)



\* : Unit ratings. Total rating=Unit rating×1.5

**Electrical Characteristics**

(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward voltage 1	V <sub>F(1)</sub>	I <sub>F</sub> =1mA	0.1	-	0.3	V
Forward voltage 2	V <sub>F(2)</sub>	I <sub>F</sub> =10mA	-	-	0.35	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =5V	-	-	0.5	μA
ESD-Capability	-	C=200pF, RL=100 Both forward reverse direction 5 pulse	225	-		V

## Electrical Characteristic Curves

Fig. 1  $I_F$ - $V_F$

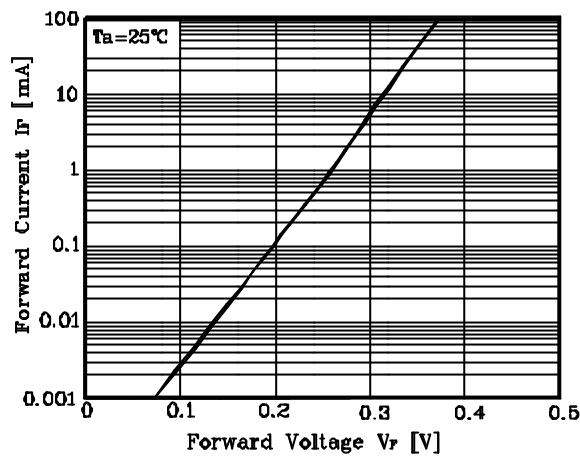


Fig. 2  $I_R$ - $V_R$

